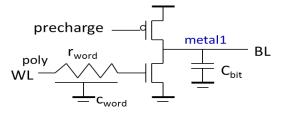
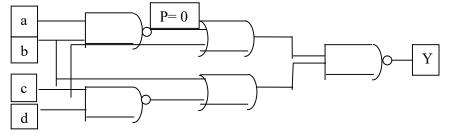
BIRLA INSTITUTE OF TECHNOLOGY, MESRA, RANCHI (END SEMESTER EXAMINATION MO/2022)

CLASS: BTECH SEMESTER: V BRANCH: ECE SUBJECT: EC325 R1DIGITAL SYSTEMS DESIGN WITH FPGAS TIME: 03 Hours FULL MARKS: 50 INSTRUCTIONS: 1. The question paper contains 5 questions each of 10 marks and total 50 marks. 2. Attempt all questions. 3. The missing data, if any, may be assumed suitably. 4. Tables/Data handbook/Graph paper etc., if applicable, will be supplied to the candidates			
Q.1(a) Q.1(b)	What are some of the most essential goals of the design's standard-cell placement and routing tools?		[2] [3]
Q.1(c)	What are the different FPGA methodologies? Explain the same with neat diagram.		[5]
Q.2 (a) Q.2 (b) Q.2(c)) Write a VHDL Code for 2 to 4 decoder using if else statement?		[2] [3] [5]
Q.3 (a) Q.3 (b) Q.3(c)	Mention a couple of the adder's optimization schemes? What are data paths in digital processor architectures? Design a transmission gate adder circuit and explain its features.		[2] [3] [5]
Q.4(a) Q.4(b) Q.4(c)	Outline the several types of memory. Implement and demonstrate the operation of the MOS cell's NOR ROM. Evaluate the propagation delay associated with NOR ROM. Resi 0.15ohm, wire capacitance/cell: 0.65 <i>f</i> F and 0.83 <i>f</i> F, and gate capacitance/cell: 0.65 <i>f</i> F and 0.83 <i>f</i> F, and gate capacitance/cell: 0.65 <i>f</i> F and 0.83 <i>f</i> F, and gate capacitance/cell: 0.65 <i>f</i> F and 0.83 <i>f</i> F, and gate capacitance/cell: 0.65 <i>f</i> F and 0.83 <i>f</i> F, and gate capacitance/cell: 0.65 <i>f</i> F and 0.83 <i>f</i> F, and gate capacitance/cell: 0.65 <i>f</i> F and 0.83 <i>f</i> F, and gate capacitance/cell: 0.65 <i>f</i> F and 0.83 <i>f</i> F, and gate capacitance/cell: 0.65 <i>f</i> F and 0.83 <i>f</i> F, and gate capacitance/cell: 0.65 <i>f</i> F and 0.83 <i>f</i> F, and gate capacitance/cell: 0.65 <i>f</i> F and 0.83 <i>f</i> F, and gate capacitance/cell: 0.65 <i>f</i> F and 0.83 <i>f</i> F, and gate capacitance/cell: 0.65 <i>f</i> F and 0.83 <i>f</i> F, and gate capacitance/cell: 0.65 <i>f</i> F and 0.83 <i>f</i> F, and gate capacitance/cell: 0.65 <i>f</i> F and 0.83 <i>f</i> F, and gate capacitance/cell: 0.65 <i>f</i> F and 0.83 <i>f</i> F, and gate capacitance/cell: 0.65 <i>f</i> F and 0.83 <i>f</i> F, and gate capacitance/cell: 0.65 <i>f</i> F and 0.83 <i>f</i> F, and gate capacitance/cell: 0.65 <i>f</i> F and 0.83 <i>f</i> F, and gate capacitance/cell: 0.65 <i>f</i> F and 0.83 <i>f</i> F, and gate capacitance/cell: 0.65 <i>f</i> F and 0.83 <i>f</i> F, and gate capacitance/cell: 0.65 <i>f</i> F and 0.83 <i>f</i> F, and gate capacitance/cell: 0.65 <i>f</i> F and 0.83 <i>f</i> F, and gate capacitance/cell: 0.65 <i>f</i> F and 0.83 <i>f</i> F, and gate capacitance/cell: 0.65 <i>f</i> F and 0.83 <i>f</i> F, and gate capacitance/cell: 0.65 <i>f</i> F and 0.83 <i>f</i> F,	stance/cell: 35ohm and	[2] [3] [5]



- Q.5(a) Define the term d-frontiers and j-frontiers?
- Q.5(b) Determine the output Y for a stuck-at-fault at P=0.



Q.5(c) Give the different classifications of open circuit faults and briefly explain them.

[5]

[2] [3]

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